Fundamentals of Atomic Force Microscopy Part 2: Dynamic AFM Methods

Week 5, Lecture 1 Measuring Electrostatic Forces I

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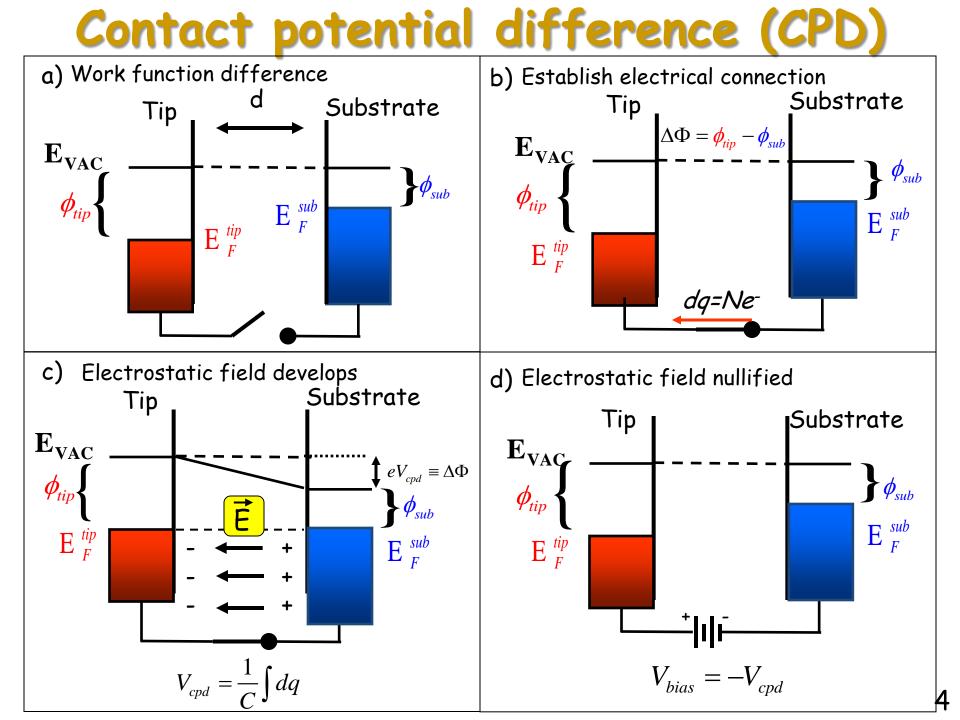
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From the last lecture

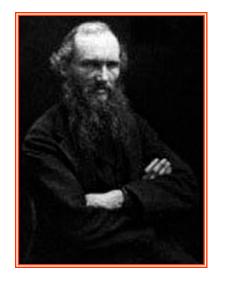
- Force reconstruction from dynamic approach curves on surfaces
- Reconstruction using both FM-AFM and AM-AFM

Electrostatic force microscopy methods

- Using oscillating metal coated AFM tip to measure or map
- Local charges on surface *
- Local dielectric constants *
- Film thickness of insulating layers *
- Photo-induced voltage *
- Contact potential difference *

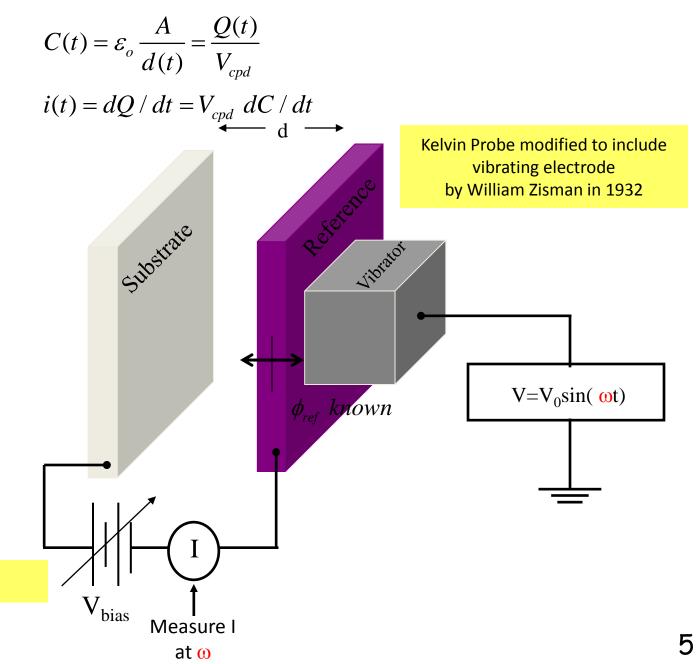


Macroscopic contact potential measurements



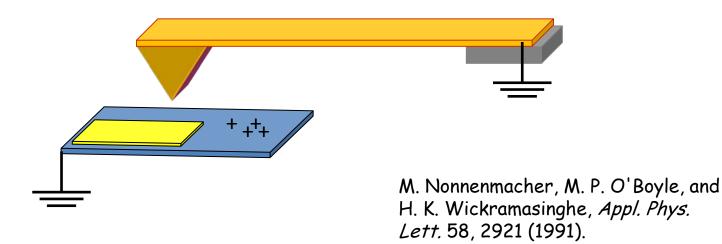
- Sir Wm. Thomson, Lord Kelvin, 1861
- Non-contact
- Non-destructive
- ~1 mV resolution (best case)

Adjust V_{bias} so I =0



Nanoscale contact potential measurements

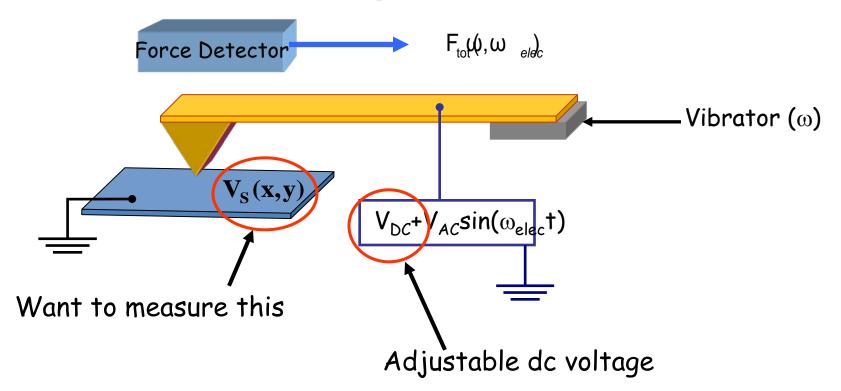
AFM cantilever -Metal coated tip or highly doped Si



For more complex samples V_{cpd} can be regarded as the Voltage required to null the electric field that develops between the tip and a local volume of the substrate. Then V_{cpd} depends on many factors

- Surface contamination of metal
- Presence of dielectrics with trapped charges
- Doping of semiconducting sample
- Thickness of dielectric layer, its dielectric constant
- For well prepared conducting samples this technique measures CPD due to difference in work-function. For more complex samples it could measure a convolution of all the above effects

Nanoscale contact potential measurements



The tip-sample potential difference (cpd) is:

 $\Delta V=V_{S}(x,y)-[V_{DC}+V_{AC}sin(\omega_{1}t)]$

 The mechanical excitation scans the topography of the sample in AM or FM-AFM while electrostatic information is collected from the electrical excitation

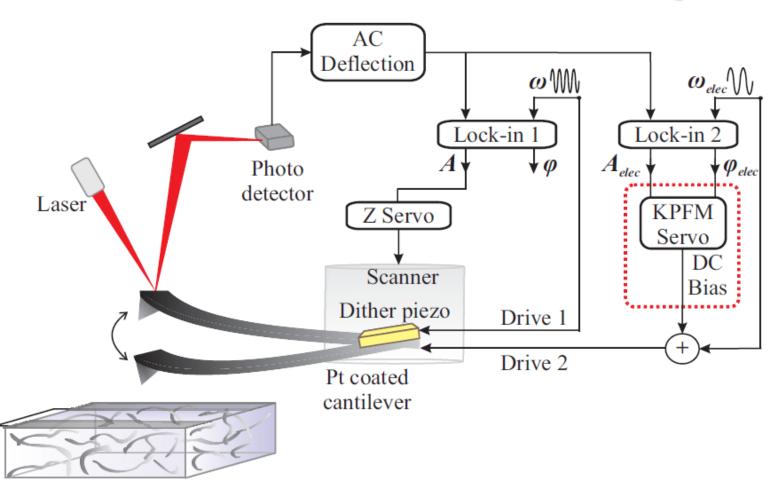
The electrostatic force channels

These forces oscillate far below the resonance frequency of the cantilever so the cantilever response at these frequencies can be written as (Appendix)

$$q_{elec}(t) = A|_{\omega_{elec}} \sin(\omega_{elec}t - \phi_{elec}) + A|_{2\omega_{elec}} \sin(2\omega_{elec}t - \hat{\phi}_{elec}) = \frac{1}{k} \left[F_{electrostatic}\Big|_{\omega_{elec}} + F_{electrostatic}\Big|_{2\omega_{elec}}\right]$$

By adjusting V_{tip} to null the vibration at ω_{elec} one can map $V_s(x, y)$ Mapping the $2\omega_{elec}$ signal allows mapping of $\frac{dC}{dz}$ over the sample

Schematic KPFM technique



- This is for the single-pass implementation (single-pass and two-pass is discussed later)
- Lock in amplifier 1 tracks the tip oscillation amplitude at the cantilever resonance
- Lock in amplifier 2 tracks the tip oscillation amplitude at the electrical excitation frequency
 ⁽ⁱ⁾elec
- The KPFM servo applies a DC bias to null the tip oscillation at ω_{elec}
- Sometimes a 3rd lock-in amplifier is used to track the signal at 2 ω_{elec}

Early results

M. Nonnenmacher, M. P. O'Boyle, and H. K. Wickramasinghe, *Appl. Phys. Lett.* 58, 2921 (1991).

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(b)	Au	Au	(e) _{Au}	Pd	
	50 nm		11 2 a	35 mV	
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				$\mathcal{F} \in \mathcal{L}$	₽Æ
(c) 1	Pt	Au	(f) _{Au}	Pd	

FIG. 2. Comparison of topographic and CPD images $(8 \mu m \times 6 \mu m)$ of different samples: (a) and (b) gold on gold, (c) and (d) platinum on gold, (e) and (f) palladium on gold.

Capable of detecting 0.1 mV of CPD!

